

# SOP-8 Plastic-Encapsulate MOSFETS

## SI4614

### N and P-Channel Enhancement Mode Power MOSFET

#### Description

The SI4614 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. The complementary MOSFETs may be used to form a level shifted high side switch, and for a host of other applications.

#### General Features

##### ● N-Channel

$$V_{DS} = 40V, I_D = 8.0A$$

$$R_{DS(ON)} < 22m\Omega @ V_{GS}=10V$$

$$R_{DS(ON)} < 31m\Omega @ V_{GS}=4.5V$$

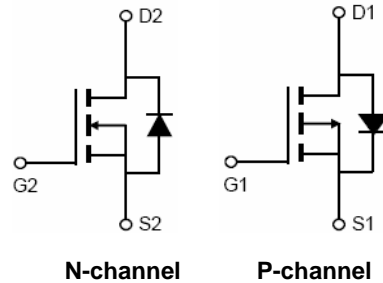
##### ● P-Channel

$$V_{DS} = -40V, I_D = -7.0A$$

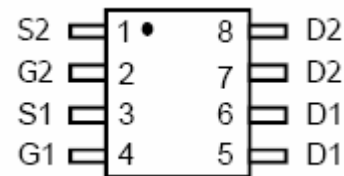
$$R_{DS(ON)} < 35m\Omega @ V_{GS}=-10V$$

$$R_{DS(ON)} < 48m\Omega @ V_{GS}=-4.5V$$

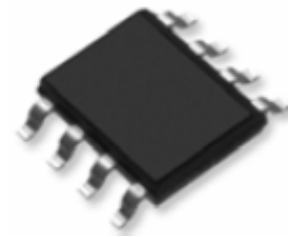
- High power and current handling capability
- Lead free product is acquired
- Surface mount package



Schematic diagram



Marking and pin assignment



SOP-8 top view

### Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		$V_{DS}$	40	-40	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	$\pm 20$	V
Continuous Drain Current	$T_A=25^\circ C$	$I_D$	8.0	-7.0	A
Pulsed Drain Current <sup>(Note 1)</sup>		$I_{DM}$	40	-30	A
Maximum Power Dissipation	$T_A=25^\circ C$	$P_D$	2.0	2.0	W
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55 To 150	-55 To 150	$^\circ C$

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient <sup>(Note2)</sup>	$R_{\theta JA}$	N-Ch	62.5	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient <sup>(Note2)</sup>	$R_{\theta JA}$	P-Ch	62.5	$^\circ C/W$

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### N-CH Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	40	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=40V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA

### On Characteristics (Note 3)

Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.4	2.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=8A$	-	17	22	m $\Omega$
		$V_{GS}=4.5V, I_D=6A$	-	21	31	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=8A$	15	-	-	S

### Dynamic Characteristics (Note 4)

Input Capacitance	$C_{iss}$	$V_{DS}=20V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	415	-	PF
Output Capacitance	$C_{oss}$		-	112	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	11	-	PF

### Switching Characteristics (Note 4)

Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=20V, R_L=2.5\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	4.0	-	nS
Turn-on Rise Time	$t_r$		-	3.0	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	15	-	nS
Turn-Off Fall Time	$t_f$		-	2.0	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=20V, I_D=8A,$ $V_{GS}=10V$	-	12	-	nC
Gate-Source Charge	$Q_{gs}$		-	3.5	-	nC
Gate-Drain Charge	$Q_{gd}$		-	3.1	-	nC

### Drain-Source Diode Characteristics

Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=8A$	-	0.75	1.0	V
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### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

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## N- Channel Typical Electrical and Thermal Characteristics (Curves)

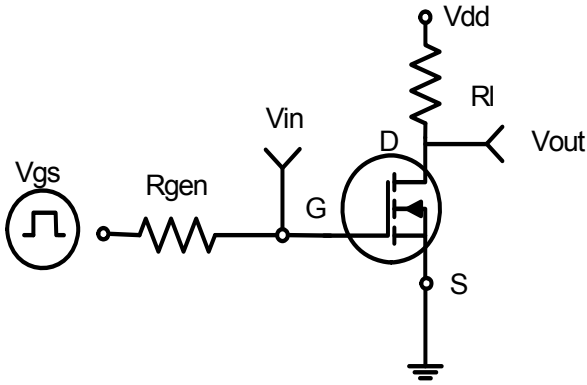


Figure 1: Switching Test Circuit

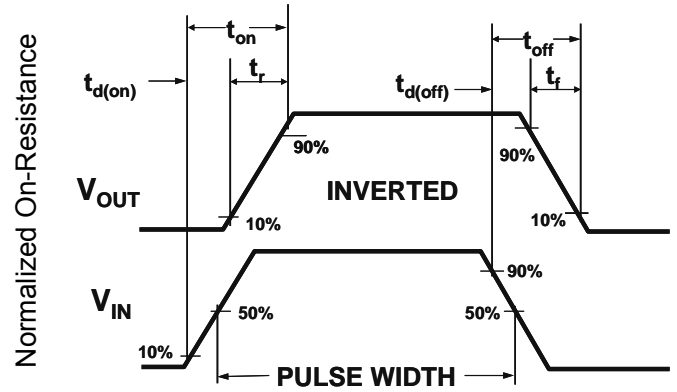


Figure 2: Switching Waveforms

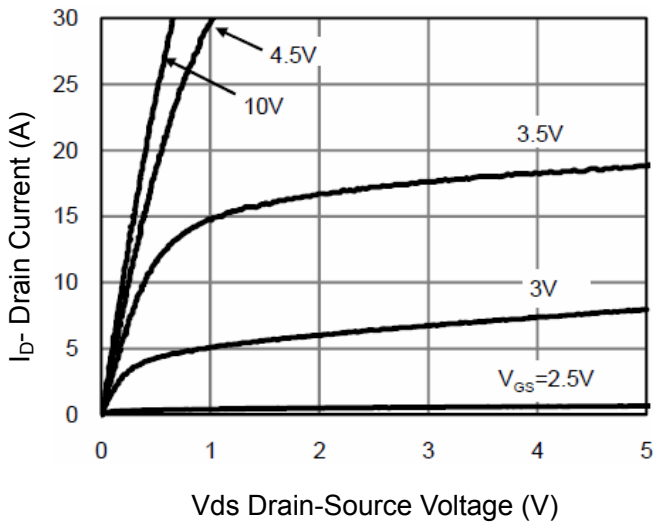


Figure 3 Output Characteristics

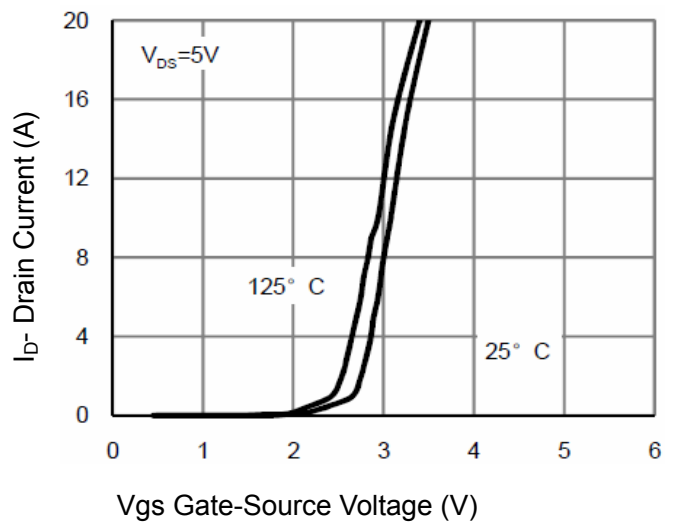


Figure 4 Transfer Characteristics

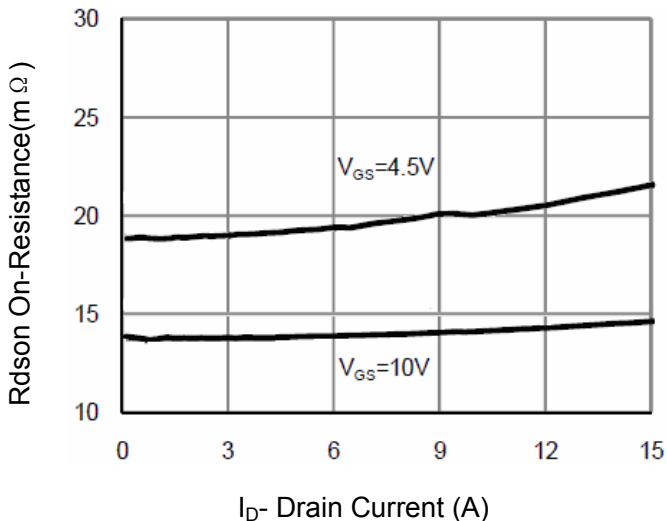


Figure 5 Drain-Source On-Resistance

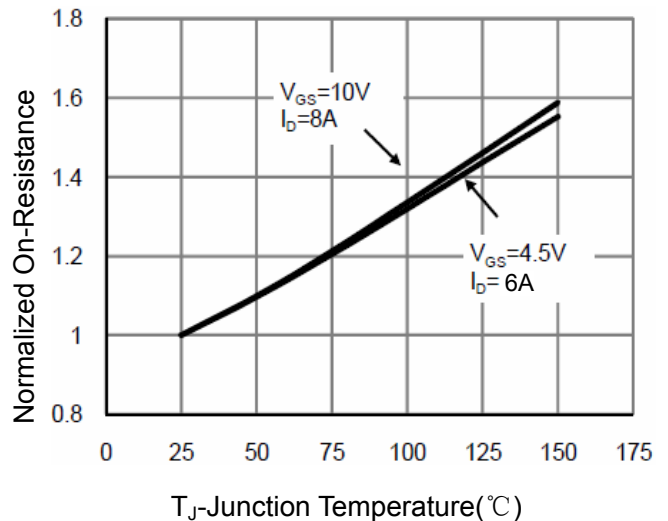
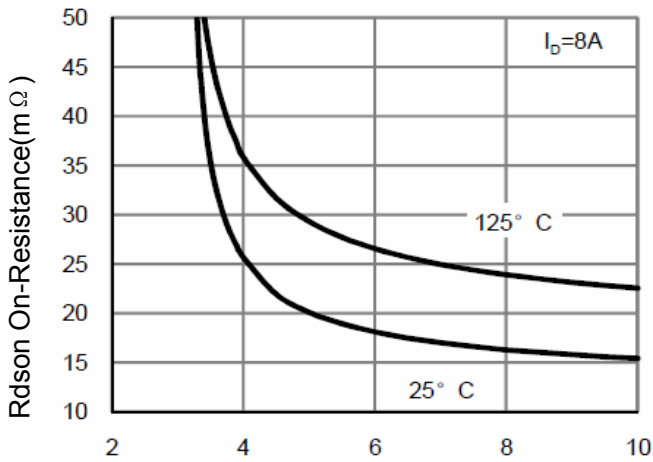


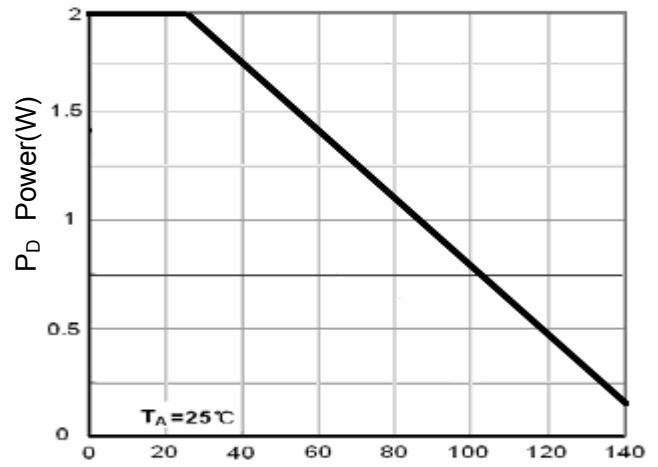
Figure 6 Drain-Source On-Resistance

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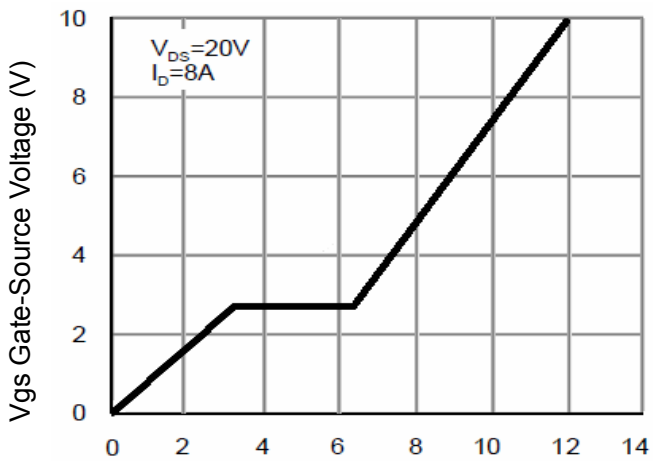
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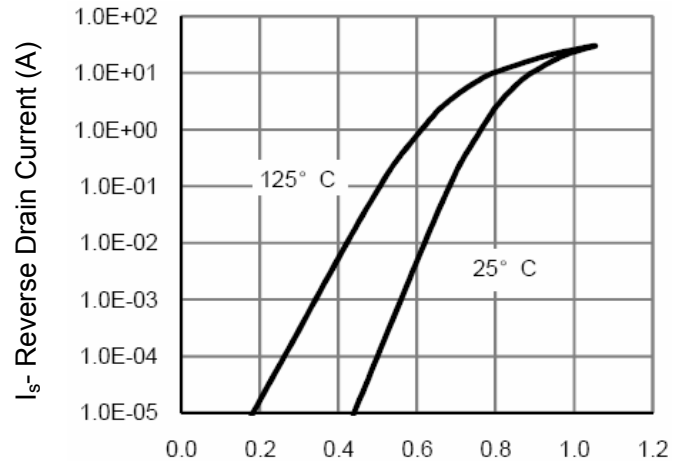
Vgs Gate-Source Voltage (V)  
**Figure 7 Rdson vs Vgs**



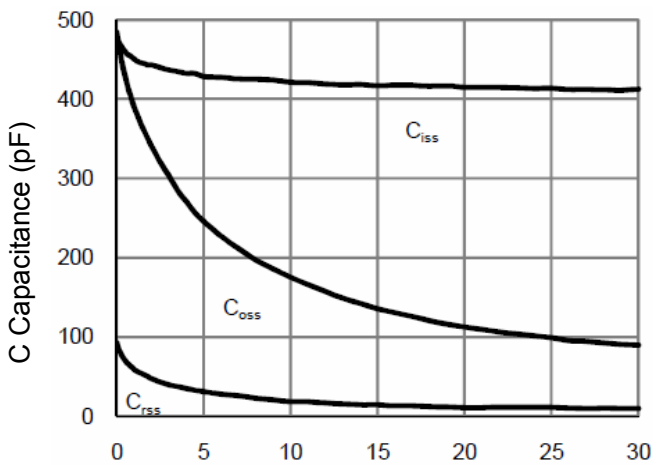
Tj Junction Temperature (°C)  
**Figure 8 Power Dissipation**



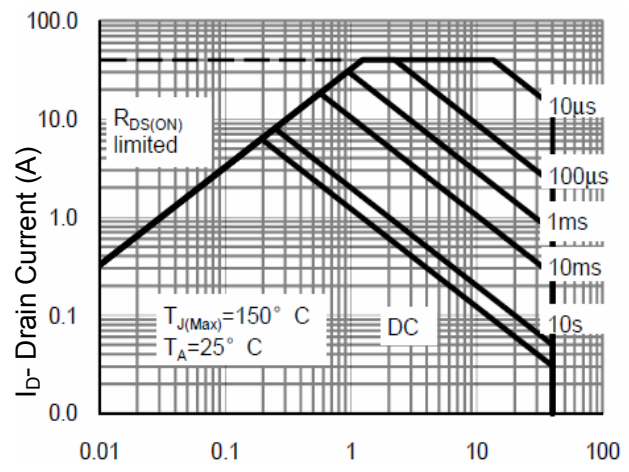
Qg Gate Charge (nC)  
**Figure 9 Gate Charge**



Vds Drain-Source Voltage (V)  
**Figure 10 Source- Drain Diode Forward**



Vds Drain-Source Voltage (V)  
**Figure 11 Capacitance vs Vds**



Vds Drain-Source Voltage (V)  
**Figure 12 Safe Operation Area**

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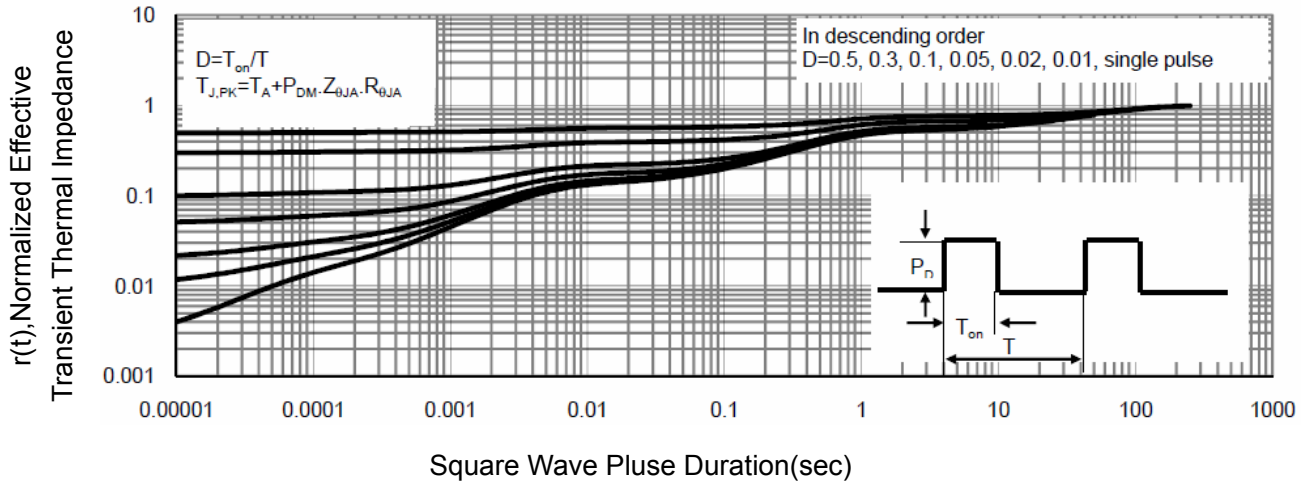


Figure 13 Normalized Maximum Transient Thermal Impedance

# SOP-8 Plastic-Encapsulate MOSFETS

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### P-CH Electrical Characteristics ( $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-40	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-40V, V_{GS}=0V$	-	-	-1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA

### On Characteristics <sup>(Note 3)</sup>

Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.1	-1.8	-2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-7.0A$	-	30	35	m $\Omega$
		$V_{GS}=-4.5V, I_D=-4.0A$	-	43	48	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=-5V, I_D=-7.0A$	15	-	-	S

### Dynamic Characteristics <sup>(Note4)</sup>

Input Capacitance	$C_{iss}$	$V_{DS}=-20V, V_{GS}=0V,$ $F=1.0MHz$	-	520	-	PF
Output Capacitance	$C_{oss}$		-	100	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	65	-	PF

### Switching Characteristics <sup>(Note 4)</sup>

Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-20V, R_L=2.3\Omega$ $V_{GS}=-10V, R_{GEN}=6\Omega$	-	7.5	-	nS
Turn-on Rise Time	$t_r$		-	5.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	19	-	nS
Turn-Off Fall Time	$t_f$		-	7	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=-20V, I_D=-7.0A$ $V_{GS}=-10V$	-	13	-	nC
Gate-Source Charge	$Q_{gs}$		-	3.8	-	nC
Gate-Drain Charge	$Q_{gd}$		-	3.1	-	nC

### Drain-Source Diode Characteristics

Diode Forward Voltage <sup>(Note 3)</sup>	$V_{SD}$	$V_{GS}=0V, I_S=-7.0A$	-	0.75	-1.0	V
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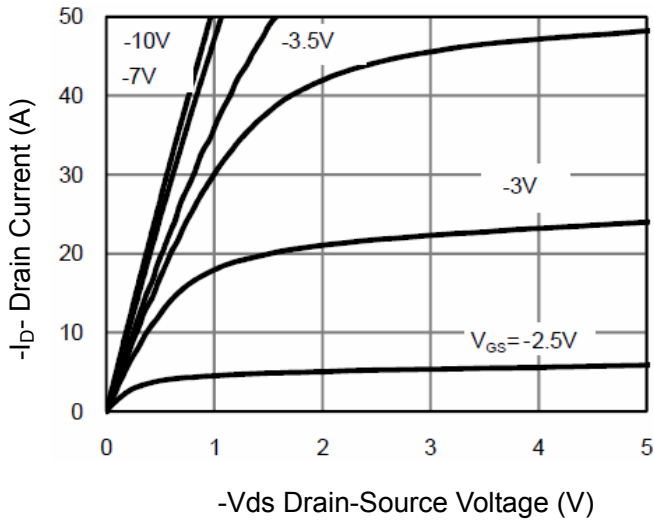
### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
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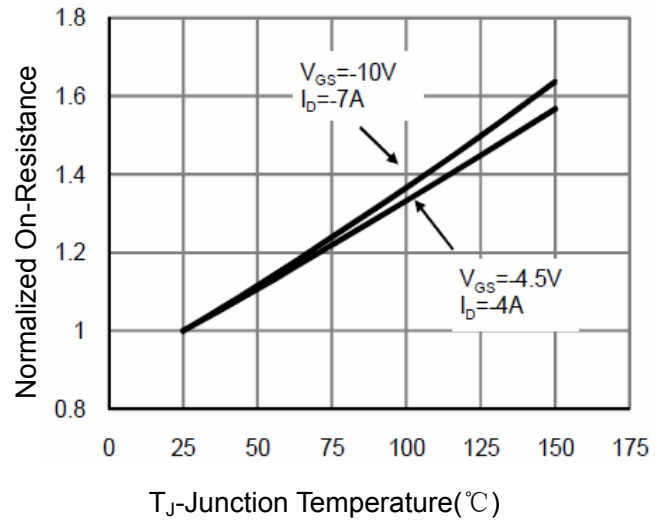
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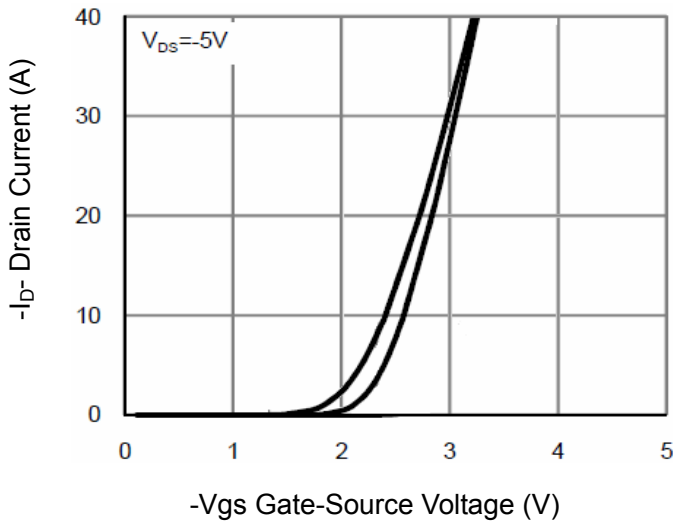
### P- Channel Typical Electrical and Thermal Characteristics (Curves)



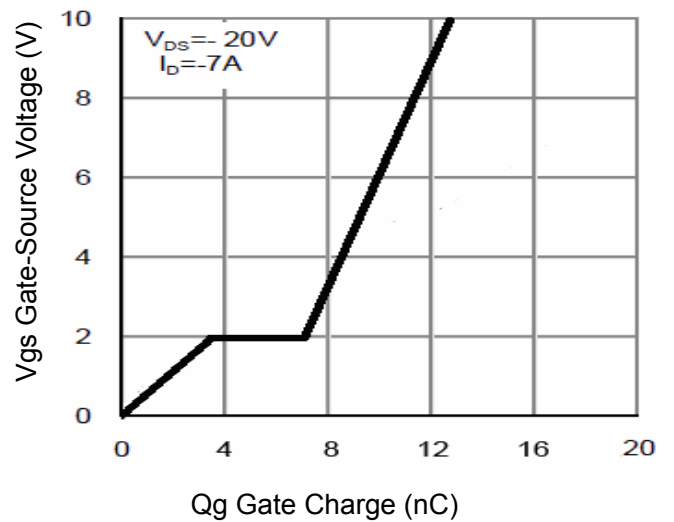
**Figure 1 Output Characteristics**



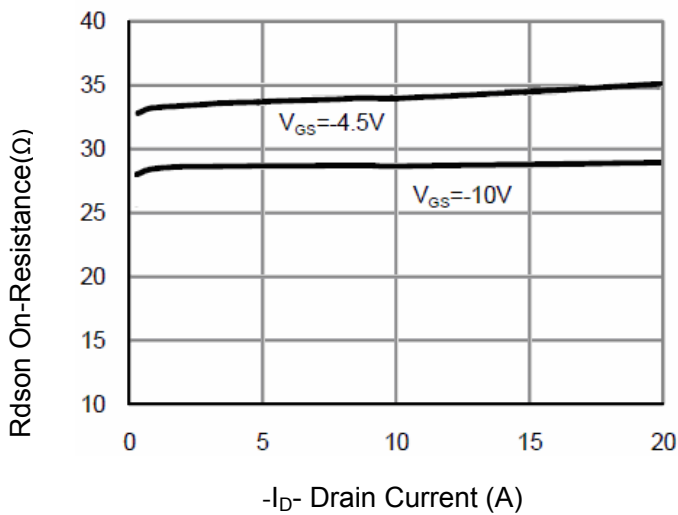
**Figure 4 Rdson-Junction Temperature**



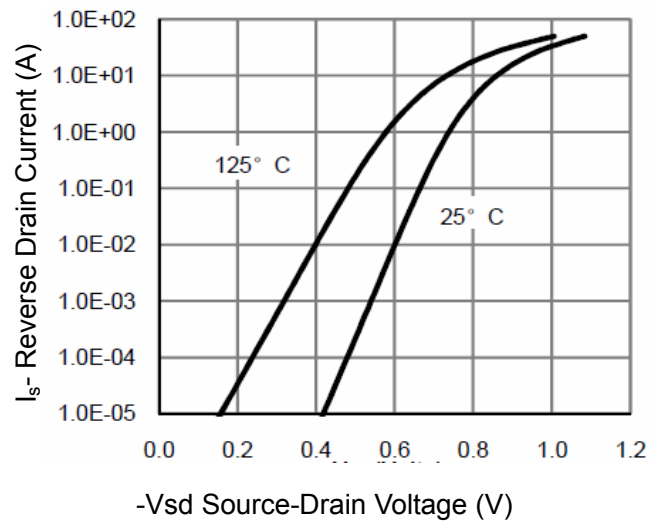
**Figure 2 Transfer Characteristics**



**Figure 5 Gate Charge**



**Figure 3 Rdson- Drain Current**



**Figure 6 Source- Drain Diode Forward**

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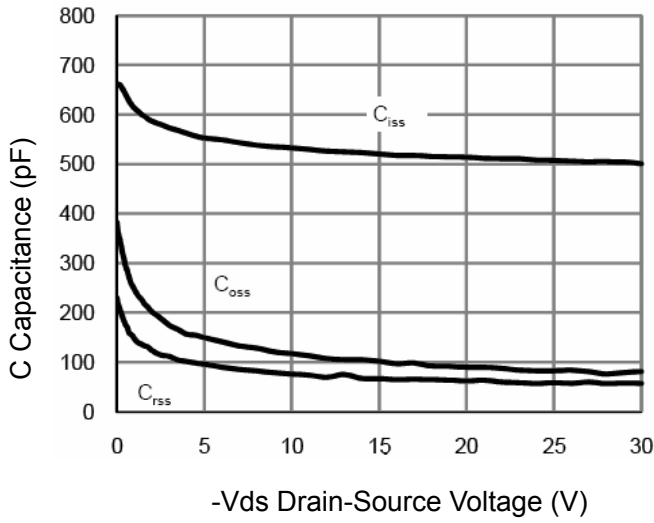


Figure 7 Capacitance vs Vds

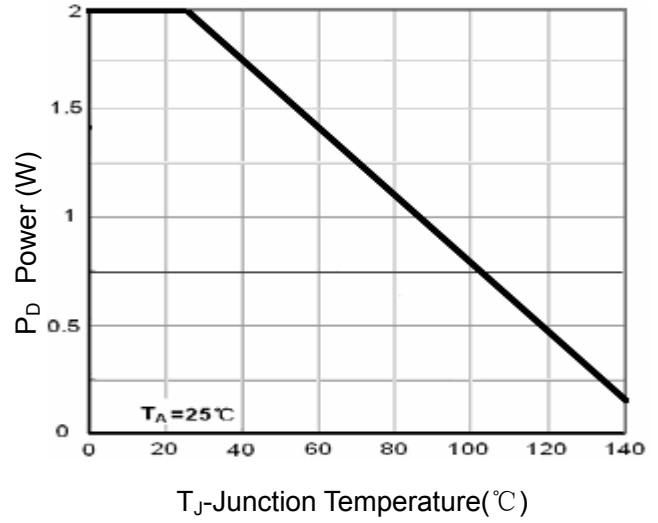


Figure 9 Power Dissipation

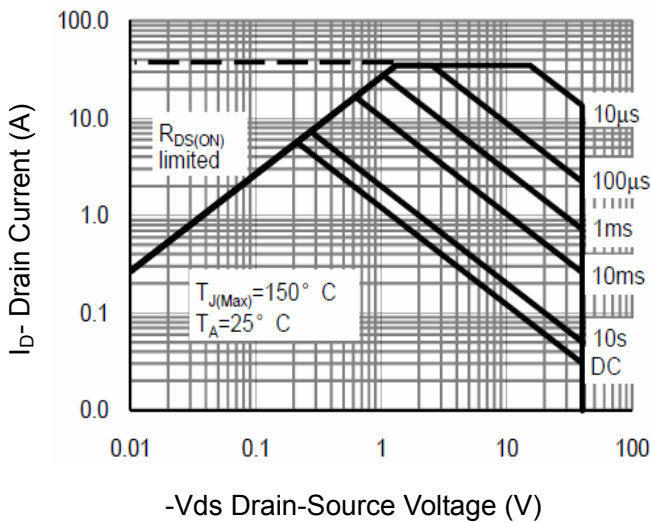


Figure 8 Safe Operation Area

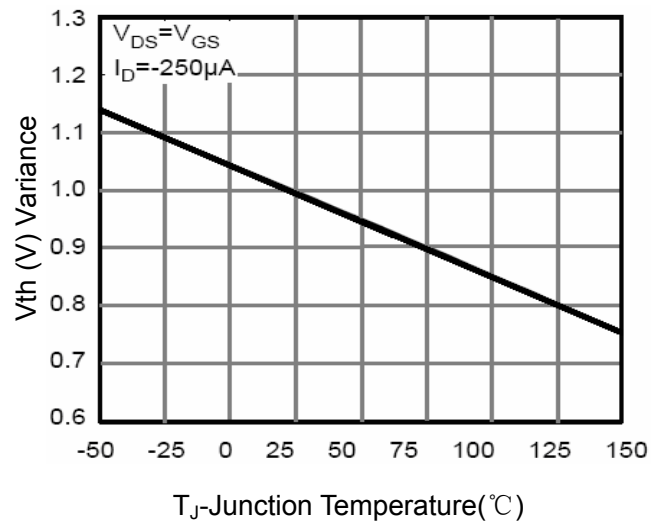


Figure 10  $V_{GS(th)}$  vs Junction Temperature

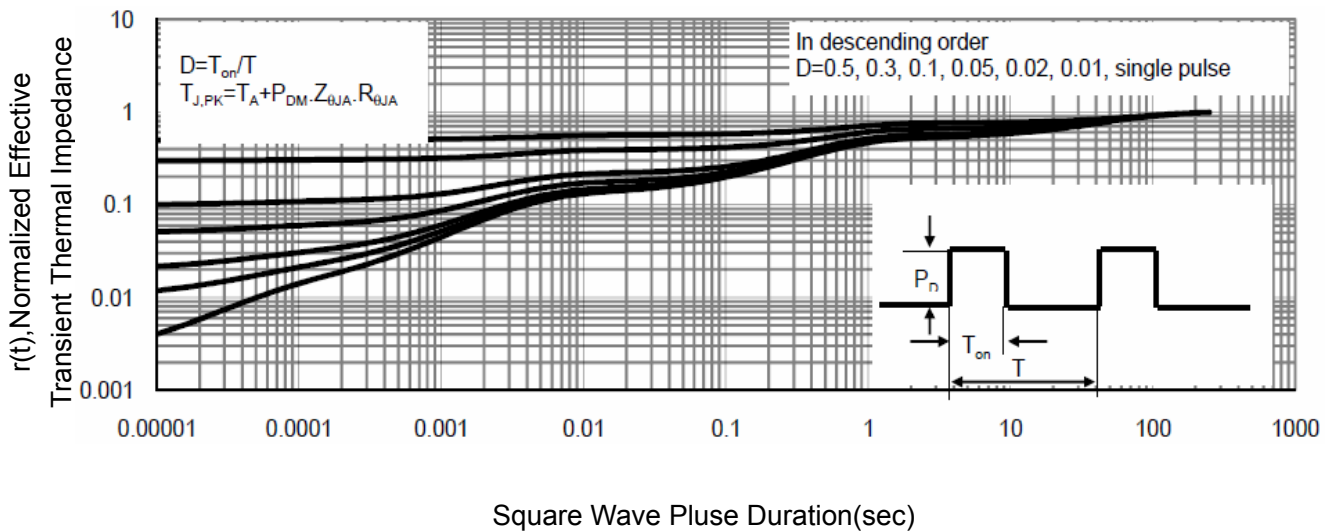


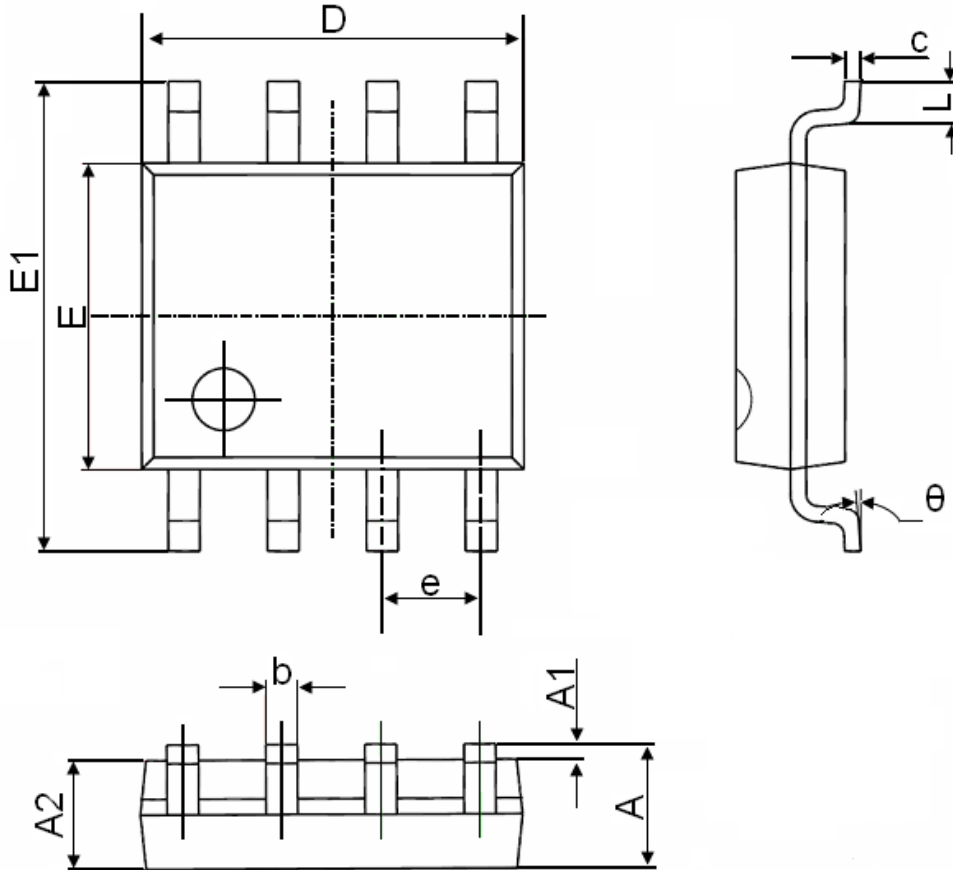
Figure 11 Normalized Maximum Transient Thermal Impedance



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## SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
$\theta$	0°	8°	0°	8°